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INFORMATION DISCLOSURE STATEMENT

Applicants: Shinji NAKAMURA et al.

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Examiner
Initial

S. Tomioka et al., "GaN Substrates with a Low Dislocation Density Grown by HVPE" In Extended Abstracts (The 61st Autumn Meeting, 2000), 9/3/00, Section 5p-Y-17, Japan Society of Applied Physics, Catalog No. AP001130-01

Examiner *Bonnie Kebede*Date Considered *11/29/2002*

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